

General Purpose Transistors

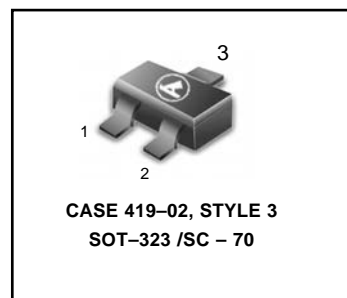
NPN Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

We declare that the material of product compliance with RoHS requirements.

S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

LMBT2222AWT1G
S-LMBT2222AWT1G

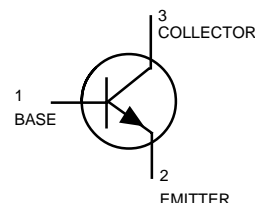


MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	75	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, $T_A = 25^\circ\text{C}$	P_D	150	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



DEVICE MARKING

LMBT2222AWT1G S-LMBT2222AWT1G = P1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (1) ($I_C = 10 \text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	$V_{(BR)CBO}$	75	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 60 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{BL}	—	20	nAdc
Collector Cutoff Current ($V_{CE} = 60 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	—	10	nAdc

1. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

LMBT2222AWT1G ;S-LMBT2222AWT1G
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS (1)				
DC Current Gain (1) ($I_C = 0.1\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 1.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 150\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 500\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	35 50 75 100 40	— — — — —	—
Collector–Emitter Saturation Voltage(1) ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{CE(sat)}$	— —	0.3 1.0	Vdc
Base–Emitter Saturation Voltage(1) ($I_C = 150\text{ mAdc}$, $I_B = 15\text{ mAdc}$) ($I_C = 500\text{ mAdc}$, $I_B = 50\text{ mAdc}$)	$V_{BE(sat)}$	0.6 —	1.2 2.0	Vdc

SMALL–SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product ($I_C = 20\text{ mAdc}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	8.0	pF
Input Capacitance ($V_{EB} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	30	pF
Input Impedance ($V_{CE} = 10\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{ie}	0.25	1.25	k Ω
Voltage Feedback Ratio ($V_{CE} = 10\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{re}	—	4.0	$\times 10^{-4}$
Small–Signal Current Gain ($V_{CE} = 10\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	75	375	—
Output Admittance ($V_{CE} = 10\text{ Vdc}$, $I_C = 10\text{ mAdc}$, $f = 1.0\text{ kHz}$)	h_{oe}	25	200	μmhos
Noise Figure ($V_{CE} = 10\text{ Vdc}$, $I_C = 100\text{ }\mu\text{Adc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	—	4.0	dB

SWITCHING CHARACTERISTICS

Delay Time	($V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = -0.5\text{ Vdc}$ $I_C = 150\text{ mAdc}$, $I_{B1} = 15\text{ mAdc}$)	t_d	—	10	ns
Rise Time		t_r	—	25	
Storage Time	($V_{CC} = 30\text{ Vdc}$, $I_C = 150\text{ mAdc}$ $I_{B1} = I_{B2} = 15\text{ mAdc}$)	t_s	—	225	ns
Fall Time		t_f	—	60	

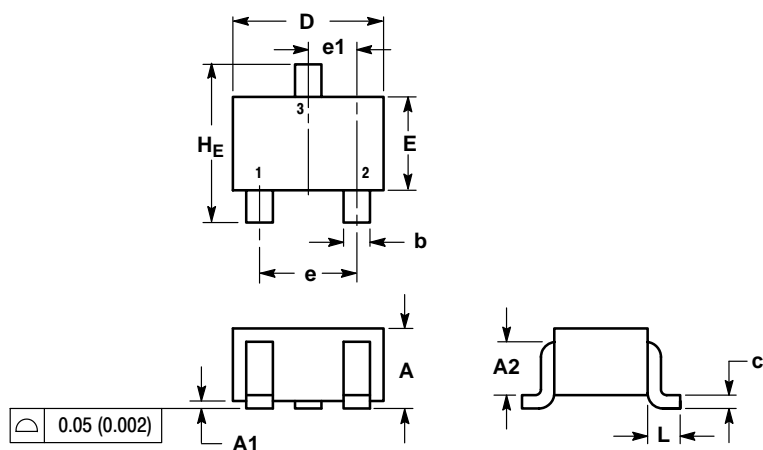
 1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

Ordering Information

Device	Marking	Shipping
LMBT2222AWT1G	P1	3000/Tape&Reel
LMBT2222AWT3G	P1	10000/Tape&Reel

LMBT2222AWT1G ;S-LMBT2222AWT1G

SC-70 (SOT-323)

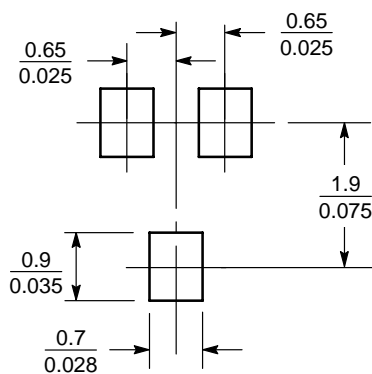


NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.7 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.425 REF			0.017 REF		
HE	2.00	2.10	2.40	0.079	0.083	0.095

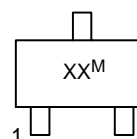
0.05 (0.002)

SOLDERING FOOTPRINT*



SCALE 10:1 (mm/inches)

GENERIC MARKING DIAGRAM



XX = Specific Device Code
 M = Date Code
 ■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present.